

ABSTRACT OF THE DISCLOSURE

5 The cleaning composition for removing resists includes a salt of hydrofluoric acid and a base not containing a metal (A component), a water-soluble organic solvent (B1 component), at least one acid selected from a group consisting of organic acid and inorganic acid (C component), water (D component), and optionally an ammonium salt (E1 component), and its hydrogen ion concentration (pH) is 4-8. Thus, in the manufacturing process of a semiconductor device such as a copper interconnecting process, removing efficiency of resist residue and other etching residue after etching or ashing improves, and corrosion resistance of copper and insulating film
10 also improves.